

# Device Modeling Report

COMPONENTS: BRT  
PART NUMBER: RN1314  
MANUFACTURER: TOSHIBA

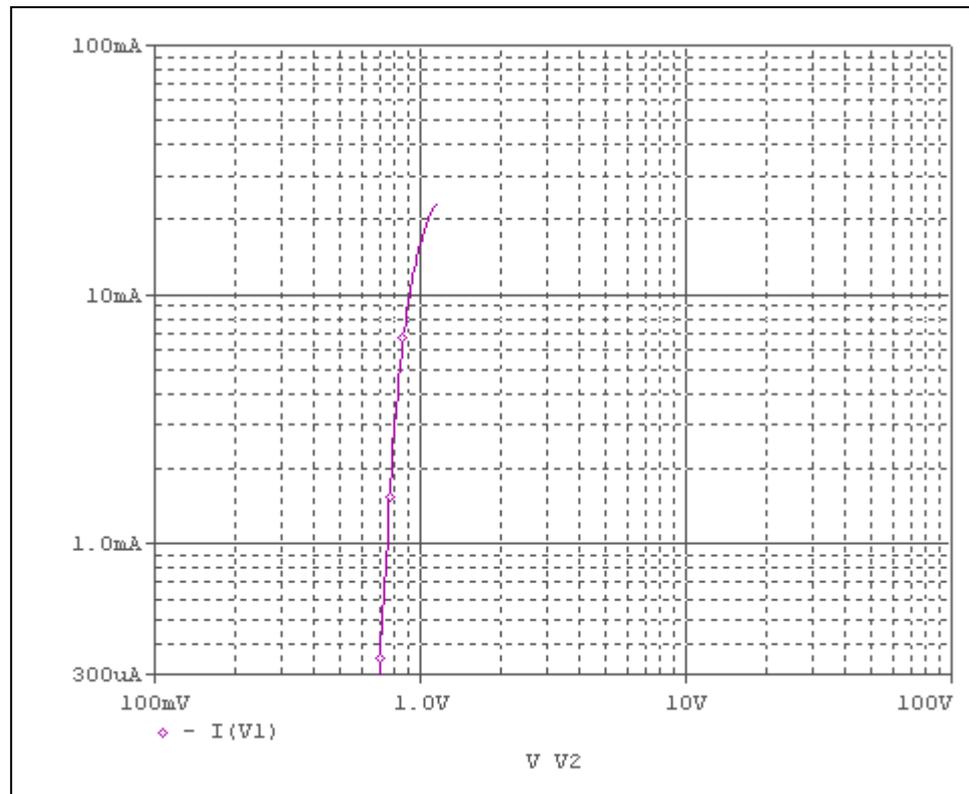


**Bee Technologies Inc.**

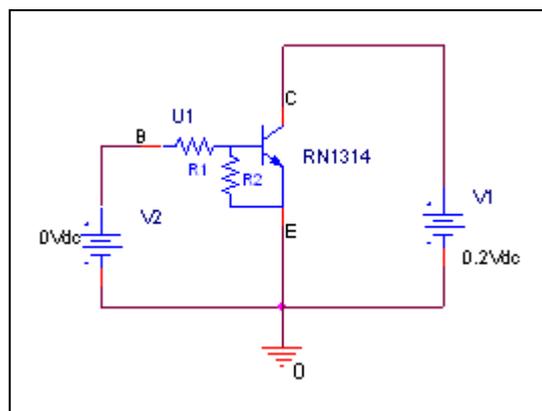
PSpice model parameter	Model description
IS	Saturation Current
BF	Ideal Maximum Forward Beta
NF	Forward Current Emission Coefficient
VAF	Forward Early Voltage
IKF	Forward Beta Roll-off Knee Current
ISE	Non-ideal Base-Emitter Diode Saturation Current
NE	Non-ideal Base-Emitter Diode Emission Coefficient
BR	Ideal Maximum Reverse Beta
NR	Reverse Emission Coefficient
VAR	Reverse Early Voltage
IKR	Reverse Beta Roll-off Knee Current
ISC	Non-ideal Base-Collector Diode Saturation Current
NC	Non-ideal Base-Collector Diode Emission Coefficient
NK	Forward Beta Roll-off Slope Exponent
RE	Emitter Resistance
RB	Base Resistance
RC	Series Collector Resistance
CJE	Zero-bias Emitter-Base Junction Capacitance
VJE	Emitter-Base Junction Potential
MJE	Emitter-Base Junction Grading Coefficient
CJC	Zero-bias Collector-Base Junction Capacitance
VJC	Collector-base Junction Potential
MJC	Collector-base Junction Grading Coefficient
FC	Coefficient for Onset of Forward-bias Depletion Capacitance
TF	Forward Transit Time
XTF	Coefficient for TF Dependency on Vce
VTF	Voltage for TF Dependency on Vce
ITF	Current for TF Dependency on Ic
PTF	Excess Phase at $f=1/2\pi*TF$
TR	Reverse Transit Time
EG	Activation Energy
XTB	Forward Beta Temperature Coefficient
XTI	Temperature Coefficient for IS

## Input voltage vs. output current (ON characteristics)

### Circuit simulation result

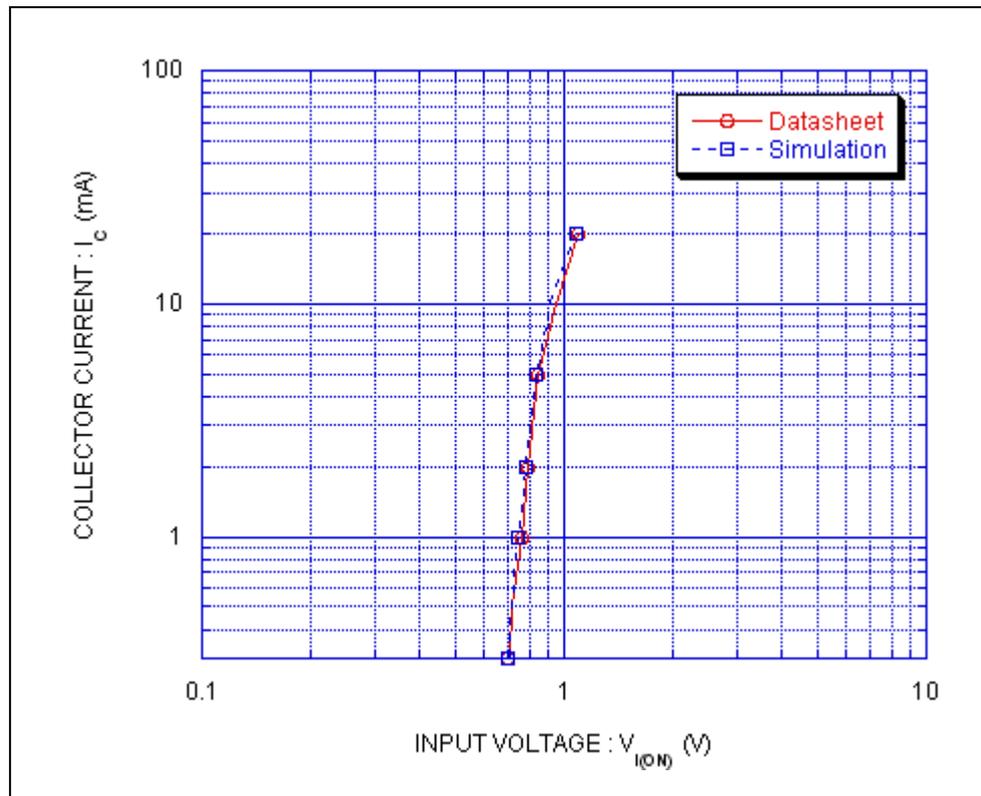


### Evaluation circuit



## Comparison Graph

### Circuit Simulation Result



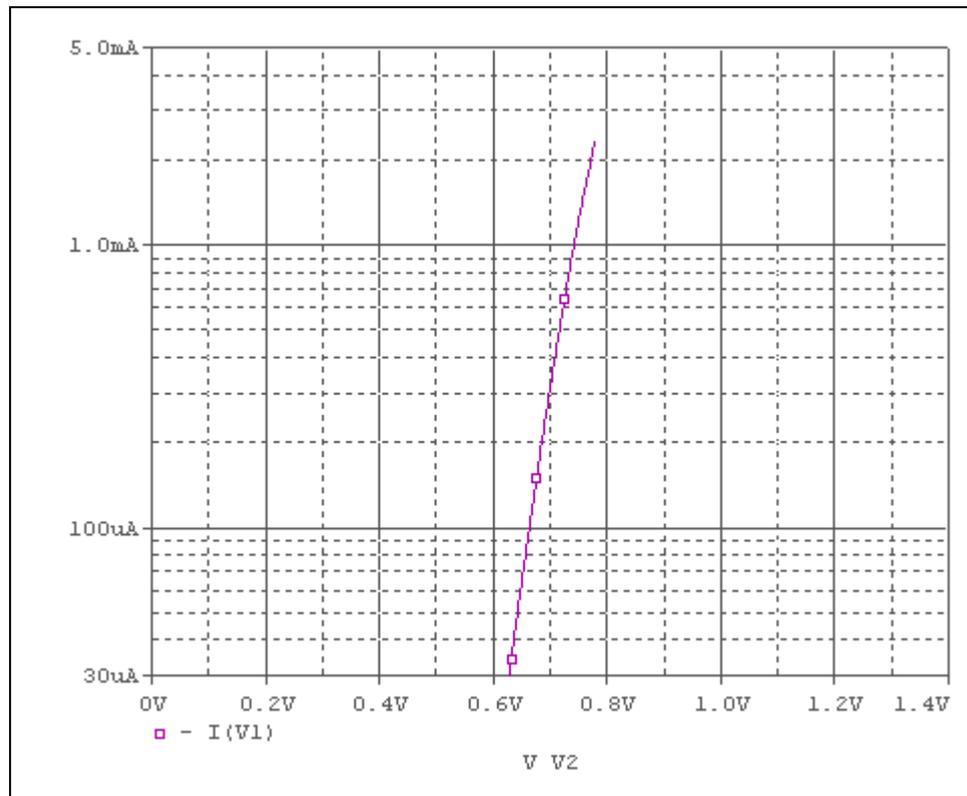
### Simulation Result

#### Condition @ $V_{ce} = 0.2$ V

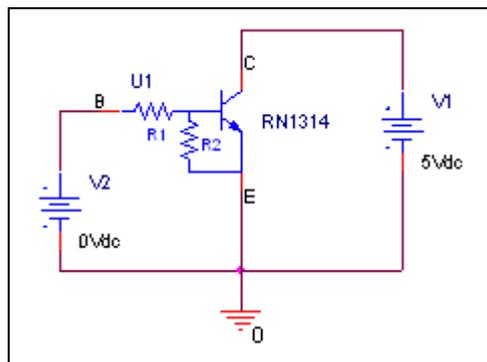
$I_c$ (mA)	$V_{I(ON)}$ (V)		Error (%)
	Datasheet	Simulation	
0.3	0.7	0.701843	0.2633
0.5	0.72	0.720154	0.0214
1	0.76	0.747803	-1.6049
2	0.79	0.779855	-1.2842
5	0.85	0.838041	-1.4069
10	0.95	0.911652	-4.0366
20	1.1	1.0748	-2.2909

## Output current vs. input voltage (OFF characteristics)

Circuit simulation result

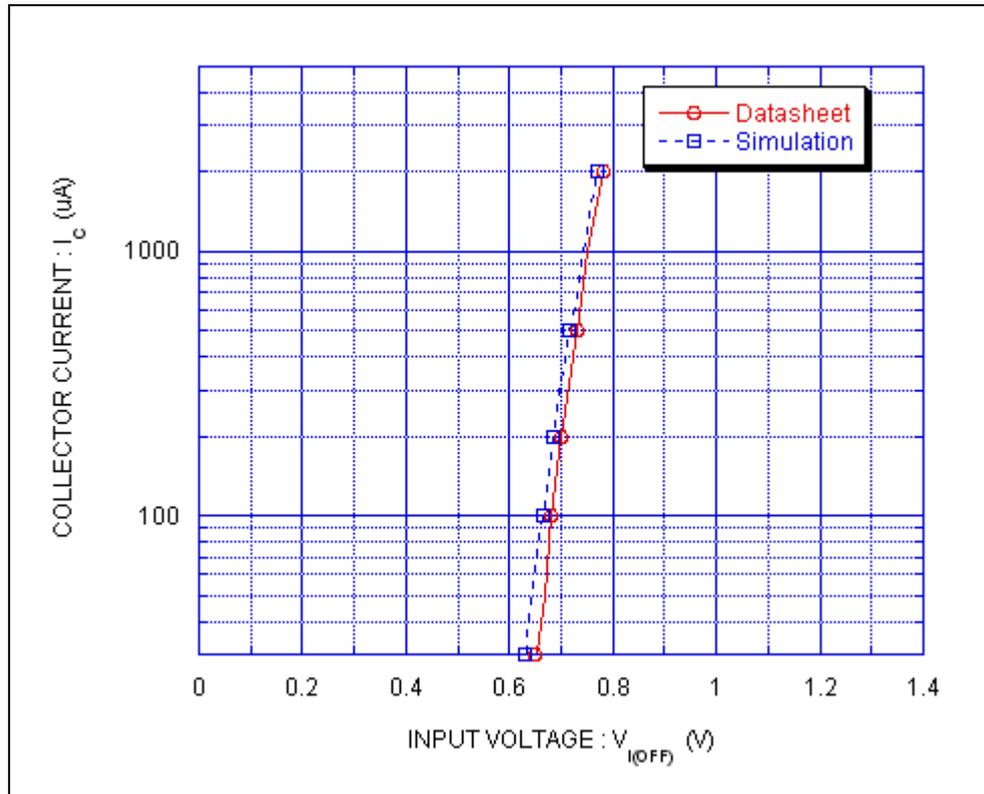


Evaluation circuit



## Comparison Graph

### Circuit Simulation Result



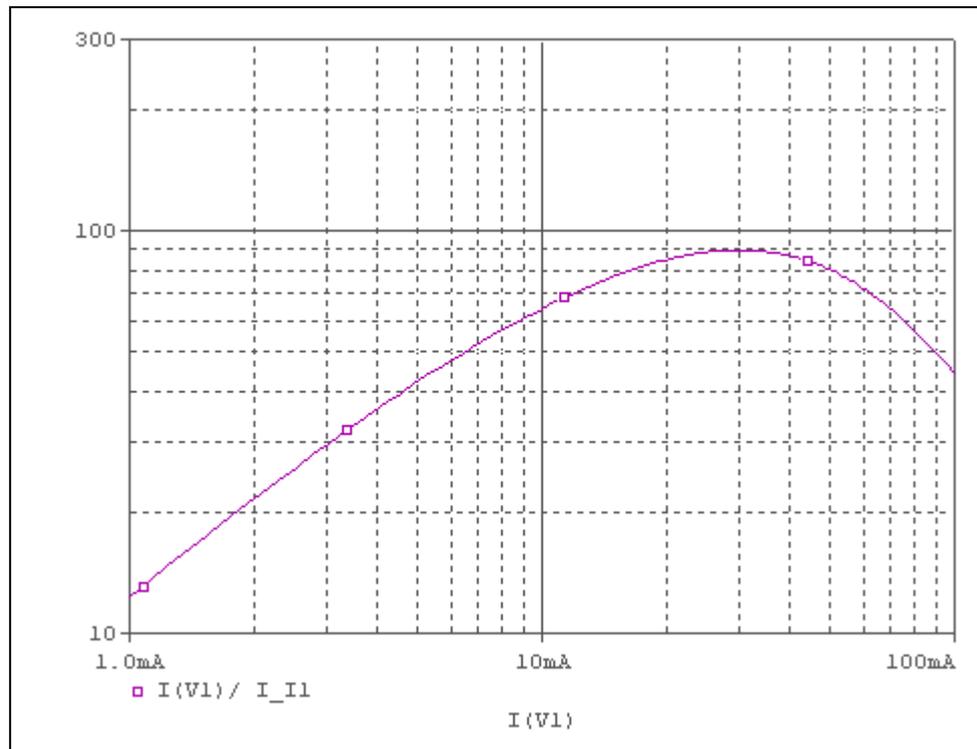
### Simulation Result

Condition @  $V_{ce} = 5 V$

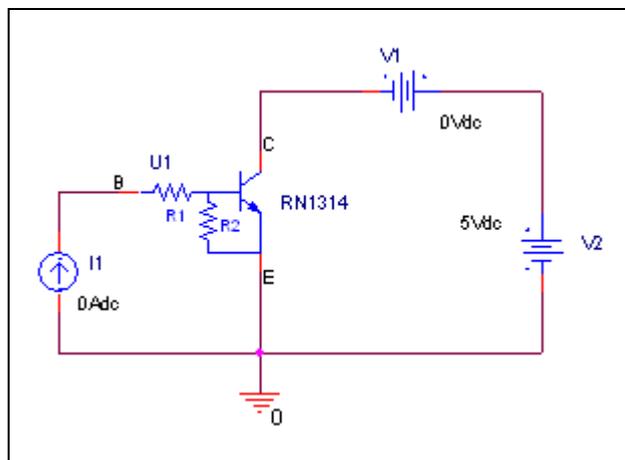
$I_c(\mu A)$	$V_{I(OFF)} (V)$		Error (%)
	Datasheet	Simulation	
30	0.65	0.628800	-3.2615
50	0.67	0.642835	-4.0545
100	0.68	0.663857	-2.3740
200	0.70	0.685628	-2.0531
500	0.73	0.716238	-1.8852
1000	0.75	0.742103	-1.0529
2000	0.78	0.771998	-1.0259

## DC current gain vs. output current

### Circuit simulation result

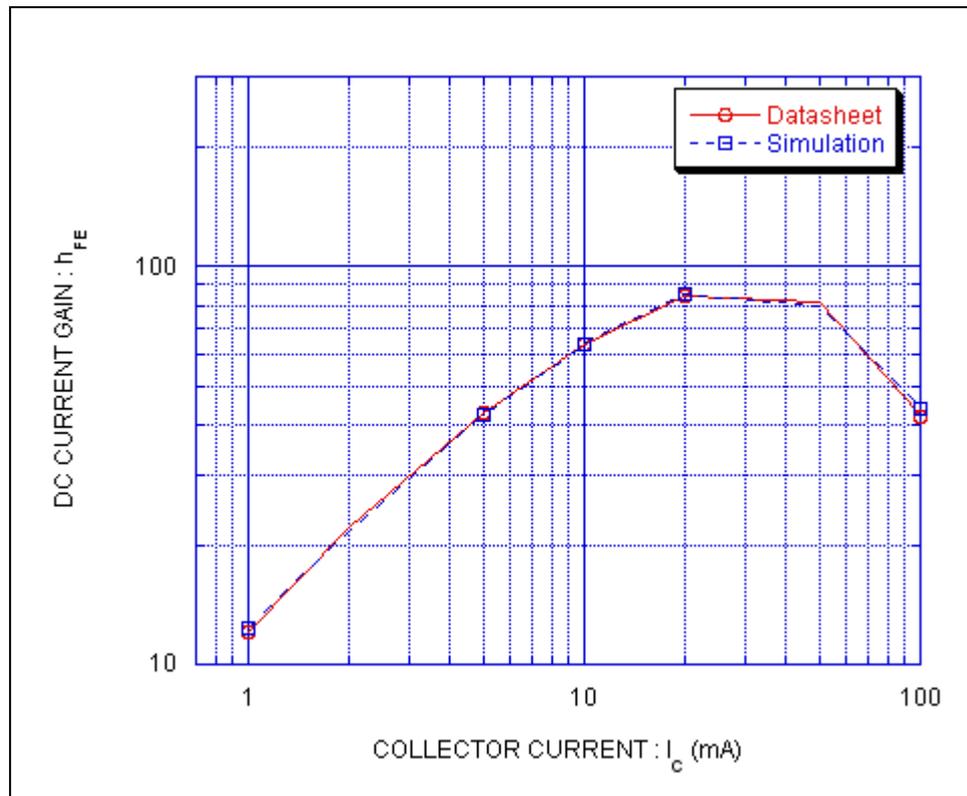


### Evaluation circuit



## Comparison Graph

### Circuit Simulation Result



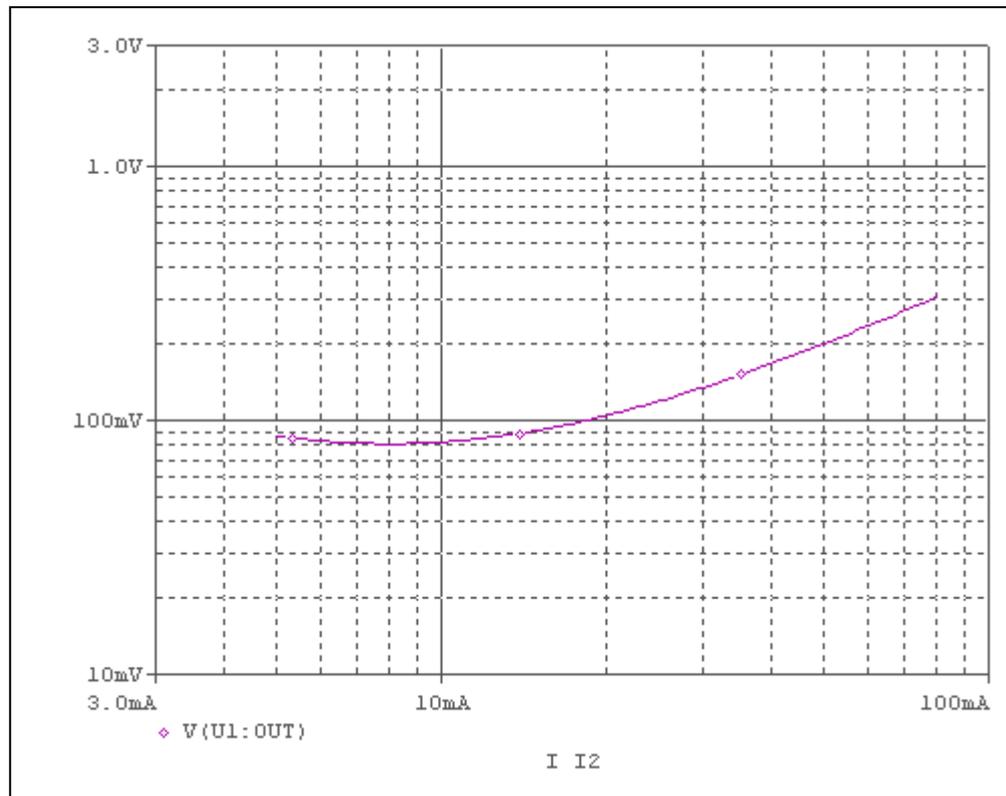
### Simulation Result

Condition @ Vce = 5 V

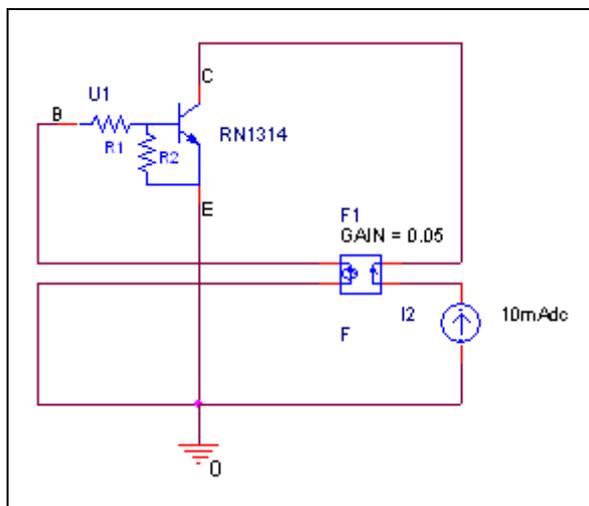
Ic(mA)	hFE		Error (%)
	Datasheet	Simulation	
1	12	12.277	2.3083
2	22	21.646	-1.6091
5	43	42.250	-1.7442
10	64	64.075	0.1172
20	84	84.879	1.0464
50	81	79.782	-1.5037
100	42	43.701	4.0500

## Output voltage VS. output current

### Circuit simulation result

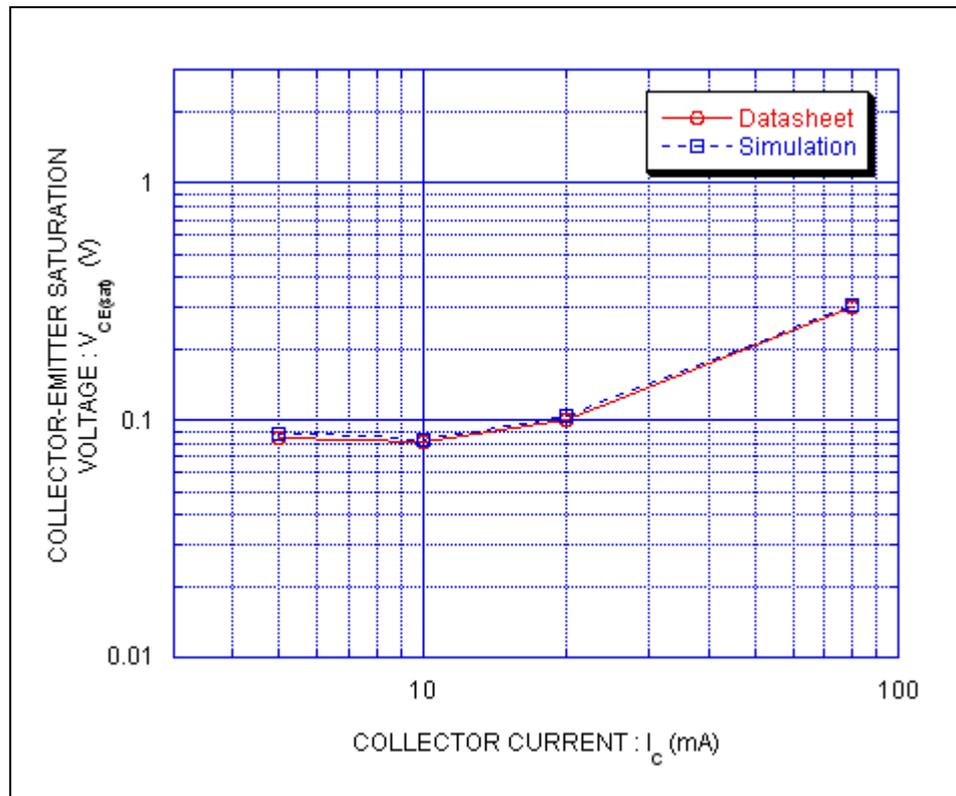


### Evaluation circuit



## Comparison Graph

### Circuit Simulation Result



### Simulation Result

Condition @  $I_C/I_B = 20$

$I_C$ (mA)	$V_{CE}$ (sat) (mV)		Error (%)
	Datasheet	Simulation	
5	0.084	0.08700	3.5714
10	0.081	0.082247	1.5395
20	0.1	0.104543	4.5430
80	0.302	0.305359	1.1123